



Infrared Thin Film Radiation Source JSIR350-4-CB-0-S5.0-0-0

Fast radiation source in SMD-housing for use with thermopiles and pyroelectric detectors in NDIR gas analysis and other applications.

Spectral Output Range ¹	typ. 1 ... 20	μm
Active Area	2.2 x 2.2	mm ²
Hot Resistant	40±20	Ω
Temperature Coefficient	typ. 650	ppm/K
Time Constant	typ. 15	ms
Nominal Power Consumption	0.65	W
Operation Voltage ²	typ. 4.9	V
Operation Current ²	typ. 132	mA
Active Area Temperature ^{3,5}	640	°C
Window	-	
Mass	~1	g
Housing	SMD	
Lifetime ⁴	> 5,000 h at 740°C > 100,000 h at 640°C	

¹ without window

² with 40Ω

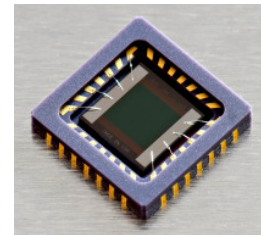
³ at nominal power (0.65W)

⁴ at 10 Hz, 50% duty cycle, preliminary results

⁵ at T_{amb} = 25°C

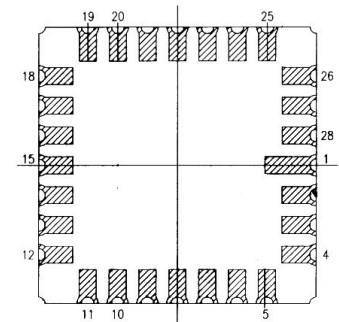


MICRO-HYBRID



Pin Assignment

Bottom View



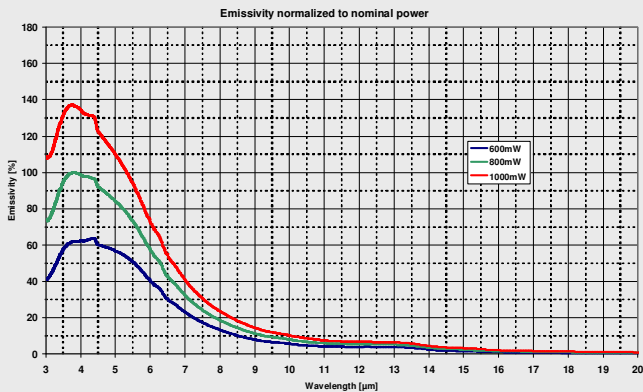
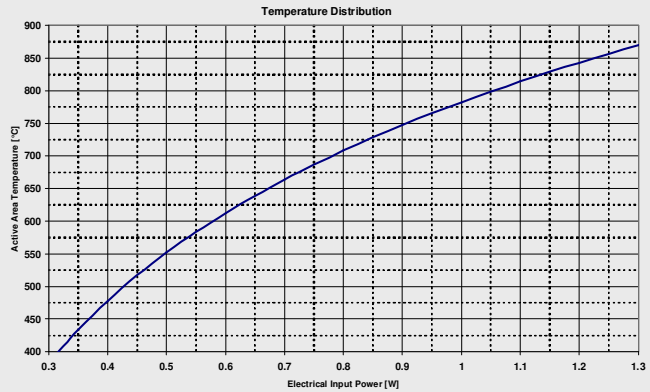
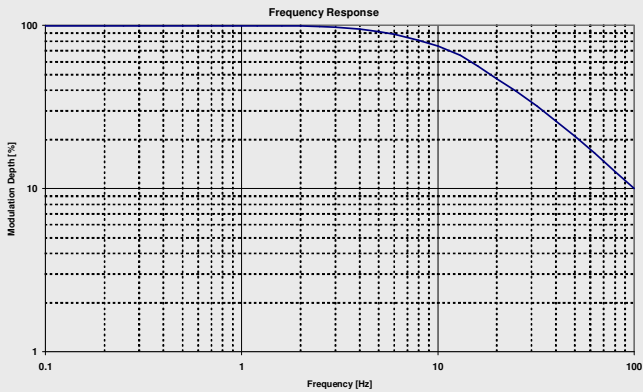
Pad

12, 14, 16, 18 Power

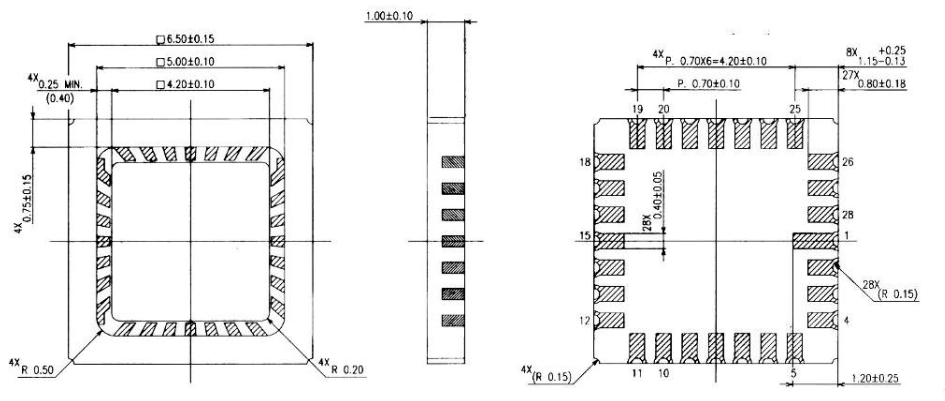
2, 4, 26, 28 Power

Absolute Max. Ratings		
Power	1.2	W
Housing temperature	200	°C
Active Area Temperature	850	°C

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Housing



Optional parts

Window – For hermetic sealing and / or spectral narrowing of the radiation

Evaluation Kit – For independent evaluation of emitters and detectors